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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
Patent Application

Inventor(s): Ho-Yuan Yu

Application No.: 10/816,980

Group Art Unit:

Filed: 04/02/04

Examiner:

Title: METHOD AND STRUCTURE FOR COMPOSITE TRENCH FILL

Form 1449

U.S. Patent Documents

| Examiner Initial | No. | Patent No. | Date | Patentee | Class | Sub-class | Filing Date |
|------------------|-----|------------|------|----------|-------|-----------|-------------|
| | A | | | | | | |

Foreign Patent or Published Foreign Patent Application

| Examiner Initial | No. | Document No. | Publication Date | Country or Patent Office | Class | Sub-class | Translation | |
|------------------|-----|--------------|------------------|--------------------------|-------|-----------|-------------|----|
| | | | | | | | Yes | No |
| | B | | | | | | | |

Other Documents

| Examiner Initial | No. | Author, Title, Date, Place (e.g. Journal) of Publication |
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| Examiner <i>MS</i> | | Date Considered 4/14/05 |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered.
Include copy of this form with next communication to applicant.